

Table I. UWBG semiconductors discovered identified by theory and progress of material synthesis. SC no., E_g , method for E_g , $m_{e/h}$, and $\mu_{e/h}$ indicate space group, calculated band gap, type of functional used to calculate band gap within density functional theory, calculated electron/hole effective mass, and calculated electron/hole mobility, respectively. The theory data is from refs.[1–5]

Materials	Crystal structure	SG no.	E_g (eV)	Method for E_g	Carrier Type	$m_{e/h}$ (m_e)	$\mu_{e/h}$ ($\text{cm}^2 \text{V}^{-1} \text{s}^{-1}$)	Type of sample for synthesized material	Ref.
HfGeO ₄	Orthorhombic	88	6.62	GW	<i>n</i>	0.067	-	Bulk	[6]
Y ₂ Si ₂ O ₇	Monoclinic	12	7.55		<i>n</i>	0.077	-	Bulk	[7]
MgSiN ₂	Orthorhombic	33	6.13		<i>n</i>	0.044	-	Thin film (epitaxy)	[8]
Al ₄ CaO ₇	Monoclinic	15	7.28		<i>n</i>	0.058	-	Bulk	[9]
ZnSiO ₃	Rhombohedral	148	6.46		<i>n</i>	0.048	-	Bulk	[10]
In ₂ Si ₂ O ₇	Monoclinic	12	5.47		<i>n</i>	0.049	-	Bulk	[11]
HfSiO ₄	Tetragonal	141	8.34		<i>n</i>	4.053	-	Bulk	[12]
Al ₂ ZnO ₄	Spinel	227	6		<i>n</i>	0.24	1284	Powder	[13]
GeO ₂	Orthorhombic	58	3.9	GGA+U	<i>n</i>	0.23	1513	Bulk	[14]
GaInO ₃	Orthorhombic	194	3.3		<i>n</i>	0.24	1235	Powder	[15]
In ₂ Ge ₂ O ₇	Spinel	227	3.2		<i>n</i>	0.33	616	Bulk	[16]
In ₂ Ge ₂ O ₇	Monoclinic	12	4		<i>n</i>	0.27	691	Thin film (poly-crystalline)	[17]
In ₂ Si ₂ O ₇	Spinel	227	3.8		<i>n</i>	0.32	811	Bulk	[18]
InBO ₃	Rhombohedral	167	4.8		<i>n</i>	0.25	959	Thin film (poly-crystalline)	[19]
Mg ₂ GeO ₄	Spinel	227	5.3		<i>n</i>	0.23	1293	Bulk	[20]
Zn ₂ SiO ₄	Rhombohedral	122	4.7		<i>n</i>	0.21	1335	Thin film (poly-crystalline)	[21]
ZnSnO ₃	Rhombohedral	148	3.4		<i>n</i>	0.24	953	Powder	[22]
ZnSnO ₃	Rhombohedral	161	3.2		<i>n</i>	0.23	1269	Thin film (epitaxy)	[23]
Zn ₄ B ₆ O ₁₃	Cubic	217	5.4		<i>n</i>	0.37	435	Bulk	[24]
Ba ₂ GeHfO ₆	Double perovskite	225	3.94	Meta-GGA	<i>n</i>	0.45	-	-	
Ba ₂ PrTaO ₆		225	3.74		<i>n</i>	0.69	-	-	
Ba ₂ PmSbO ₆		225	4.28		<i>n</i>	0.38	-	-	
Ba ₂ SnHfO ₆		225	4.36		<i>n</i>	0.37	-	-	
GeO ₂	Rutile	136	4.68	HSE	<i>n</i> <i>p</i>	0.27 1.31	288.33 27.98	Thin film (epitaxy)	[25]
SiO ₂	Rutile	136	8.57	HSE	<i>p</i>	1.31	-	Bulk	[26]
LiGaO ₂	Orthorhombic	33	5.1	HSE	<i>n</i>	0.4	-	Thin film (epitaxy)	[27]

References

1. E. M. Garrity, C.-W. Lee, P. Gorai, M. B. Tellekamp, A. Zakutayev, and V. Stevanović, *PRX Energy* **1**, 033006 (2022).
2. H. Shen, J. Wu, Z. Chen, X. Fang, J. Li, W. Li, J. Lin, F. Zhu, X. Wang, and Y. Chen, *J. Phys. Chem. C* **127**, 21410 (2023).
3. K. Bushick, K. A. Mengle, S. Chae, and E. Kioupakis, *Appl. Phys. Lett.* **117**, 182104 (2020).
4. K. Dabsamut, A. Boonchun, and W. R. L. Lambrecht, *J. Phys. D: Appl. Phys.* **53**, 274002 (2020).
5. P. Gorai, R. W. McKinney, N. M. Haegel, A. Zakutayev, and V. Stevanovic, *Energy Environ. Sci.* **12**, 3338 (2019).
6. A. Ennaciri, A. Kahn, and D. Michel, *J. Less Common Met.* **124**, 105 (1986).
7. Z. Sun, Y. Zhou, and M. Li, *J. Mater. Res.* **21**, 1443 (2006).
8. C. Hu, V. Gopal, T. Vangipuram, C. Chae, I. K. Turan, N. Hoven, W. R. L. Lambrecht, J. Hwang, Y. Ijiri, H. Zhao, and K. Kash, (2025).
9. A. N. Christensen, B. Lebech, D. Sheptyakov, and J. C. Hanson, *Acta Crystallogr. B.* **63**, 850 (2007).
10. T. Arlt and R. J. Angel, *Phys. Chem. Miner.* **27**, 719 (2000).
11. G. R. Patzke, R. Wartchow, and M. Binnewies, *New Cryst. Struct.* **215**, 15 (2000).
12. J. A. Speer and B. J. Cooper, *Am. Mineral.* **67**, 804 (1982).
13. D. Levy, A. Pavese, A. Sani, and V. Pischedda, *Phys. Chem. Miner.* **28**, 612 (2001).
14. K. Shiraki, T. Tsuchiya, and S. Ono, *Acta Crystallogr. Sect. B* **59**, 701 (2003).
15. R. D. Shannon and C. T. Prewitt, *J. Inorg. Nucl. Chem.* **30**, 1389 (1968).
16. H. Li, Y. Li, N. Li, Y. Zhao, H. Zhu, P. Zhu, and X. Wang, *RSC Adv.* **5**, 44121 (2015).
17. C.-W. Lee, K. Egbo, E. Garrity, M. Jankousky, H. Garland, A. Zakutayev, and V. Stevanović, (2025).
18. A. F. Reid, C. Li, and A. E. Ringwood, *J. Solid State Chem.* **20**, 219 (1977).
19. E. M. Garrity, K. Egbo, C. W. Lee, A. Zakutayev, and V. Stevanović, *Chem. Mater.* **35**, 9952 (2023).
20. K. Mahmood, J. Jacob, A. Rehman, A. Ali, U. Rehaman, N. Amin, S. Ikram, A. Ashfaq, and S. Hussain, *Ceram. Int.* **45**, 18701 (2019).
21. H. Ogawa, A. Kan, N. Ikeda, and A. Fujita, *Phys. B Condens. Matter* **407**, 4308 (2012).
22. D. Kovacheva and K. Petrov, *Solid State Ionics* **109**, 327 (1998).
23. H. Zhu, J. Liu, R. Chen, B. Feng, C. Luan, J. Ma, and H. Xiao, *Vacuum* **197**, 110811 (2022).

24. P. SMITH, S. GAECIA-BLANCO, and L. RIVOIR, *Cryst. Mater.* **119**, 375 (1964).
25. S. Chae, H. Paik, N. M. Vu, E. Kioupakis, and J. T. Heron, *Appl. Phys. Lett.* **117**, 072105 (2020).
26. Y. Tsuchida and T. Yagi, *Nature* **340**, 217 (1989).
27. S. Yasuhara, A. Nakagawa, K. Okamoto, T. Shiraishi, H. Funakubo, S. Yasui, M. Itoh, T. Tsurumi, and T. Hoshina, *RSC Adv.* **14**, 13900 (2024).